



**THE DATASHEET OF
ZXM41N10FTA**



Obsolete. Alternative is BSS123.

ZXM41N10F

SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL D MOSFET

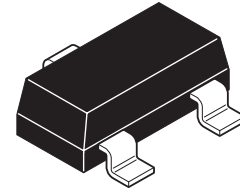
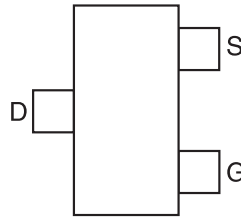
FEATURES

- $BV_{DSS} = 100V$

- Low Threshold

DEVICE MARKING

- 410



ABSOLUTE MAXIMUM RATINGS

PINOUT TOP VIEW

SOT23

PARAMETER	SYMBOL	VALUE	UNIT
Drain-source voltage	V_{DS}	100	V
Drain-gate voltage	V_{DGR}	100	V
Continuous drain current at $T_{amb}=25^{\circ}C$	I_D	170	mA
Pulsed drain current	I_{DM}	680	mA
Gate-source voltage	V_{GS}	± 20	V
Power dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	360	mW
Operating and storage temperature range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Drain-source breakdown voltage	BV_{DSS}	100			V	$I_D=0.25mA, V_{GS}=0V$
Gate-source threshold voltage	$V_{GS(th)}$	0.5		1.5	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-body leakage	I_{GSS}			50	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero gate voltage drain current	I_{DSS}			500	nA	$V_{DS}=100V, V_{GS}=0V$
Static drain-source on-state resistance ⁽¹⁾	$R_{DS(on)}$			8 12	Ω	$V_{GS}=4.5V, I_D=150mA$ $V_{GS}=3V, I_D=50mA$
Forward transconductance ⁽¹⁾⁽²⁾	g_{fs}	80			mS	$V_{DS}=25V, I_D=100mA$
Input capacitance ⁽²⁾	C_{iss}		25		pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Common source output capacitance ⁽²⁾	C_{oss}		9		pF	
Reverse transfer capacitance ⁽²⁾	C_{rss}		4		pF	
Turn-on delay time ⁽²⁾⁽³⁾	$t_{d(on)}$		10		ns	$V_{DD}=30V, I_D=280mA$
Rise time ⁽²⁾⁽³⁾	t_r		10		ns	
Turn-off delay time ⁽²⁾⁽³⁾	$t_{d(off)}$		15		ns	
Fall time ⁽²⁾⁽³⁾	t_f		25		ns	

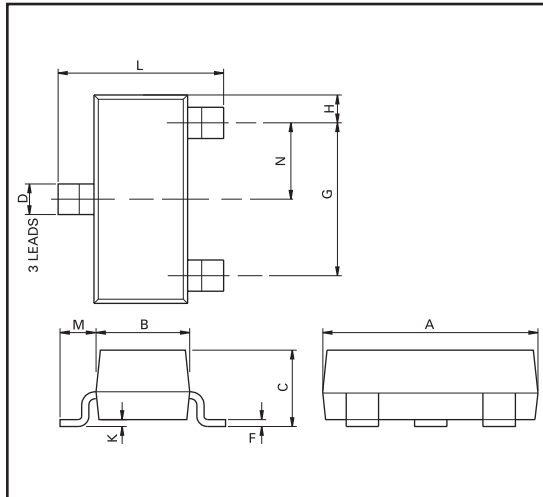
NOTES:

⁽¹⁾ Measured under pulsed conditions. Width=300 μ s. Duty cycle \leq 2% ⁽²⁾ Sample test.

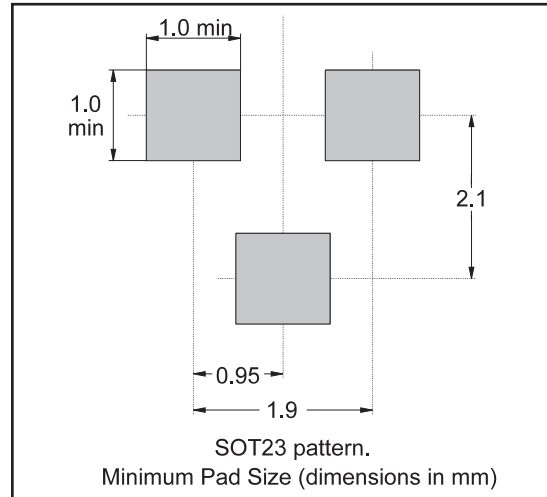
⁽³⁾ Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator

ZXM41N0F

PACKAGE OUTLINE



PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Max	Max
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		Θ	10° TYP		10° TYP	

© Zetex Semiconductors plc 2006

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Kustermann-Park Balanstraße 59 D-8541 München, Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex plc Fields New Road, Chadderton Oldham, OL9 8NP United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to www.zetex.com



ISSUE 2 - OCTOBER 2006

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

- ⊖ [View ZXM41N10FTA on WIN SOURCE](#)
- ⊖ [Diodes Incorporated Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

- ✓ Global Sourcing Solution
- ✓ Obsolete Management
- ✓ Cost Control Management
- ✓ Shortage Management
- ✓ Alternative Solution
- ✓ Excess Inventory Management